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by Richie Estrada

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ELECTRICAL PROPERTIES TEST OF DIELECTRIC CONSTANT AND IMPEDANCE CHARACTERISTIC THIN FILMS OF LiTaO₃ AND 10% Ga₂O₃ DOPED LiTaO₃

Richie Estrada¹, Nani Djohan¹, Gaby Charla Rundupadang¹, Ade Kurniawan², Johan Iskandar²,

Muhammad Dahrul², Hendradi Hardhienata² and Irzaman²

Department of Electrical Engineering, Krida Wacana Christian University, Jakarta, Indonesia

Department of Physics, Bogor Agricultural University, Bogor, Indonesia

E-Mail: richie.estrada@ukrida.ac.id

ABSTRACT

This study aims to investigate dielectric constant and impedance characteristic of thin films made from LiTaO₃ without (0%) and with doping (10%) Ga₂O₃. The solubility of LiTaO₃ for the purpose of this study is regulated at 1 M by using 2-m2 poxyethanol [(CH₃OCH₂CH₂OH)] as solvent. The growth of thin films on 7059 corning glass substrate was processed by Chemical Solution Deposition (CSD) method. By using a spin coater device on a speed of 3000 pm for 30 seconds, the substrate is then annealed in furnace at a temperature of 550 °C for eight hours. To create aluminum contacts, the thin films were then further processed by involving Metal Organic Chemical Vapor Deposition (MOCVD) technique. The final thin films weremeasured by LCR meter to provide certain data such as: inductance, capacitance and resistance values in range frequency from 50 Hz to 5 MHz. The study concludes that the film thickness (made from LiTaO₃ without (0%) and with doping (10%) Ga₂O₃) as separator material between two aluminum contacts that embedded on 7059 corning glass substrate was affected not only by dielectric constant but also by magnitude of impedance that contributes to providing information about ionic phenomenon.

Keywords: dielectric constant, impedance characteristic, thin film, LiTaO3, Ga2O3.

INTRODUCTION

Ferroelectrics are dielectric materials [1] that permanent electric dipoles which exhibit a spontaneous electric polarization even without the influence an electric field [2-4]. Furthermore, the polarization requires two steady conditions at minimum, as well as the capability to be switched from one condition to another when an electric field is applied [4]. Spontaneous polarization is obtained through the extrapolation by withdrawing line at the saturated linear region until intersecting the polarization axis [4]. Therefore, the application of an appropriate electric field not only can be reverse the direction of the polarization, but also can change the magnitude of polarization [3, 4]. In addition, the electric polarization of a material also can be influenced by temperature (called pyroelectricity), stress (called piezoelectricity) or light (called electro-opticity) [3-5].

Lithium tantalate (LiTaO3) is crystalline ferroelectric which exhibits excellent pyroelectric, piezoelectric, electro-optical and non-linear optical properties [6-8]. The crystal structure LiTaO₃(rhombohedral structure of space group R3c) is an important part to observe the electrical properties in form of dielectric and impedance on thin films [6, 8-11]. Based on literature, the electrical properties of thin film is very affected by phenomenon of ions and also dopant (fusion inside crystalline structure on substrate [12-15]. The aim of this study is to investigate the dielectric constant and impedance characteristic of each thin layer (undoped and 10% Ga₂O₁₁₀oped LiTaO₃) on 7059 corning glass substrates, using LCR meter (HIOKI 3532-50 LCR HiTESTER) as a measurement device.

METHODOLOGY

Lithium tantalate (LiTaO₃) is formed by mixing the chemicals powder between lithium acetate [Li (CH₃COO)] and tantalum pentoxide [(Ta₂O₅)] by utilizing the balance of chemical equation [16]:

 $2\text{Li}(\text{CH}_3\text{COO}) + \text{Ta}_2\text{O}_5 + 4\text{O}_2 \rightarrow 2\text{Li}\text{Ta}\text{O}_3 + 4\text{CO}_2 + 3\text{H}_2\text{O}$

Based the balance of chemical equation with solubility that has been regulated at 1 M, the mass composition of lithium acetate powder [Li(CH₃COO), 99.99% purity] is 0.1650 g and tantalum pentoxide powder [(Ta₂O₅), 99.8% purity] is 0.5524 g [16, 17]. In addition, the gallium oxide powder [(Ga₂O₃), 99.98% purity] is used as a doping with a mass of 0.0590 g (10% from the mass of LiTaO₃) [16].

The mass composition which is obtained from calculation of lithium acetate powder, tantalum pentoxide powder and gallium oxide powderwas weighed by using analytical sci (ADAM equipment). The chemicals powder is mixed and dissolved in 2.5 ml 2-methoxyethanol [(CH₃OCH₂CH₂OH)] to produce two types of solution (LiTaO₃ and LiTaO₃ + 10% Ga₂O₃). Thesolutions were sonicated by using ultrasonicator device (BRANSON 2510) for 90 minutes to obtain the homogeneous solutions.

The layer of thin film from two types of solution, which were already homogeneous on 7059 corning glass 2 bstrates dimensionless $1 \times 1 \text{ cm}^2$, were then processed by Chemical Solution Deposition (CSD) method using a spin coater on speed of 3000 rpm for 30 seconds. Each of thin layer wastreated three times coating process (deposition and rotation) with interrupt time for one

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(1)

minute, then annealed in furnace (VULCAN TM 3-130) at a temperature of 550 $^{\circ}$ C for eight hours.

The next fabrication was by creating contact made from aluminum material dimensionless 2 32 mm² at 7059 corning glass substrate and layer of thin films using Metal Organic Chemical Vapor Deposition (MOCVD) technique. The aluminum contacts were utilized as a surface for mounting the fine copper wire (see Figure-1). Probe of LCR meter (HIOKI 3532-50 LCR HITESTER) connected at the ends of fine copper wire were utilized to get the data in form of inductance, capacitance and resistance values at a range frequency of 50 Hz - 5 MHz.

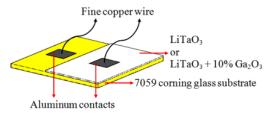


Figure-1. Structure of thin film.

RESULT AND DISCUSSIONS

In this 4 dy, the measurements of thin films were carried out on a frequency range from 50 Hz to 5 MHz, by using LCR meter (HIOKI 3532-50 LCR HITESTER) and presented in the form of curves inductance, capacitance and resistage as a function of frequency (seeFigure-2, Figure-4). The dielectric constant of thin films can be calculated by using the following formula (1) [9]:

with:

C = capacitance value (from measurement values)
d = film thickness
$$(1 \times 10^{-6} \text{ m})$$
 ϵ_0 = the vacuum permittivity $(8.8542 \times 10^{-12} \text{ F/m})$
A = aluminum contact surface area $(4 \times 10^{-6} \text{ m}^2)$

0.01
0.008
0.004
0.002
0 1000000 20000000 30000000 40000000 50000000

Frequency (Hz)

Figure-2. Curve of inductance as a function of frequency.

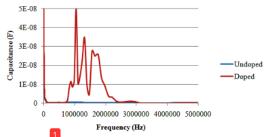


Figure-3. Curve of capacitance as a function of frequency.

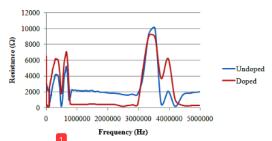


Figure-4. Curve of resistance as a function of frequency.

Formula (1) implies that the dielectric constantas a function of frequency can be presented in form of curve (Figure-5). Figure-5 shows that Ga₂O₃ as doping material can produce fluctuation of dielectric constant value and therefore, it is concluded that ion from Ga₂O₃ experiencing vibrations inside the crystal structure of LiTaO₃.

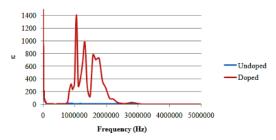


Figure-5. Curve of dielectric constant as a function of frequency.

Impedance (denoted Z) is a complex number with resistance as real part and reactance (inductive and capacitive) as imaginary part. Based on measurement values of inductance, capacitance and resistance as a function of frequency (see Figure-2, Figure-4), the magnitude of impedance (|Z|) for thin films at each frequency can be calculated by using the following formula (2), (3) and (4) [10]:

$$X_{L} = 2 \pi f L \tag{2}$$

$$X_{C} = \frac{1}{2\pi fC} \tag{3}$$

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$$|Z| = \sqrt{R^2 + (X_L - X_C)^2}$$
 (4)

with:

f = frequency (from 50 Hz to 5 MHz)

L = inductance value (from measurement values)

C = capacitance value (from measurement values)

R = resistance value (from measurement values)

 X_L = inductive reactance X_C = capacitive reactance

Formula (4) implies that the magnitude of impedance as a function of frequency can be presented in form of curve (Figure-8). Figure-8 shows that fluctuation curve of thin films between undoped and $10\%\ Ga_2O_3$ doped LiTaO_3 describes the ion motion on specific range frequency.

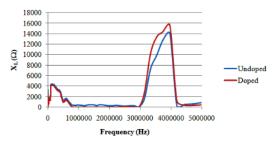


Figure-6. Curve of X_L as a function of frequency.

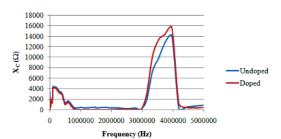


Figure-7. Curve of X_C as a function of frequency.

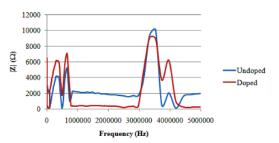


Figure-8. Curve of |Z| as a function of frequency.

CONCLUSIONS

In this study, the curve that represents dielectric constant and impedance values of thin film is used to describe ionic vibration, as well as ionic motion corresponds to a change of frequency on a range of 50 Hz to5 MHz. Based on the results of this study, it can be concluded that the film thickness (made from LiTaO₃ without (0%) and with doping (10%) Ga₂O₃) as separator material between two aluminum contacts that embedded on 7059 corning glass substrate was affected not only by dielectric constant but also by magnitude of impedance that contributes to providing information about ionic phenomenon.

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